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SGA-3586(Z)

Package: SOT-86

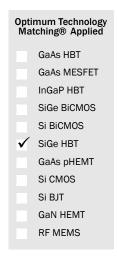
DC to 5000 MHz, CASCADABLE SiGe HBT MMIC AMPLIFIER

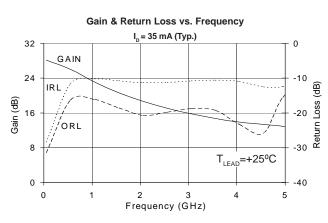
RFMD Green, RoHS Compliant, Pb-Free (Z Part Number)



Product Description

The SGA-3586 is a high performance SiGe HBT MMIC Amplifier. A Darlington configuration featuring one-micron emitters provides high F_T and excellent thermal performance. The heterojunction increases breakdown voltage and minimizes leakage current between junctions. Cancellation of emitter junction non-linearities results in higher suppression of intermodulation products. Only two DC-blocking capacitors, a bias resistor, and an optional RF choke are required for operation.





Features

- High Gain: 25dB at 850MHz
- Cascadable 50Ω Gain Block
- High Output IP₃: 25dBm typ. at 1950MHz
- Low Noise Figure: 2.5dB typ. at 1950MHz
- Low Current Draw: 35 mA typ.
- Single Voltage Supply Operation

Applications

- PA Driver Amplifier
- Cellular, PCS, GSM, UMTS
- IF Amplifier
- Wireless Data, Satellite

Parameter	Specification			Unit	Condition		
raiailletei	Min. Typ. Max.		Condition				
Small Signal Gain	22.5	25.0	27.5	dB	850MHz		
	18.0	20.0	22.0	dB	1950MHz		
		18.5		dB	2400 MHz		
Output Power at 1dB Compression		13.0		dBm	850MHz		
	11.0	12.5		dBm	1950MHz		
Output Third Intercept Point		24.5		dBm	850 MHz		
	23.0	25.0		dBm	1950MHz		
Bandwidth Determined by Return Loss		5000		MHz	>10dB		
Input Return Loss	9.5	11.0		dB	1950MHz		
Output Return Loss	14.0	20.0		dB	1950MHz		
Noise Figure		2.5	3.5	dB	1950MHz		
Device Operating Voltage	3.0	3.25	3.5	V			
Device Operating Current	31	35	39	mA			
Thermal Resistance (Junction - Lead)		97		°C/W			

Test Conditions: $I_D = 35 \,\text{mA}$ Typ., $I_{LEAD} = 25 \,^{\circ}$ C, $I_{S} = I_{LEAD} = 25 \,^{\circ}$ C, $I_{S} = I_{LEAD} = 100 \,^{\circ}$ Tone Spacing = 1 MHz

DS100629

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Absolute Maximum Ratings

Parameter	Rating	Unit
Max Device Current (I _D)	70	mA
Max Device Voltage (V _D)	6	V
Max RF Input Power	+18	dBm
Max Junction Temp (T _J)	+150	°C
Operating Temp Range (T _L)	-40 to +85	°C
Max Storage Temp	+150	°C

Operation of this device beyond any one of these limits may cause permanent damage. For reliable continuous operation, the device voltage and current must not exceed the maximum operating values specified in the table on page one. Bias Conditions should also satisfy the following expression: $I_DV_D < (T_J - T_L) / R_{TH}, j - I_J > I_J >$



Caution! ESD sensitive device.

Exceeding any one or a combination of the Absolute Maximum Rating conditions may cause permanent damage to the device. Extended application of Absolute Maximum Rating conditions to the device may reduce device reliability. Specified typical performance or functional operation of the device under Absolute Maximum Rating conditions is not implied.

RoHS status based on EUDirective 2002/95/EC (at time of this document revision).

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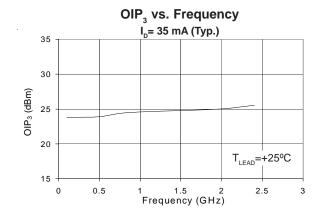
Typical Performance at Key Operating Frequencies

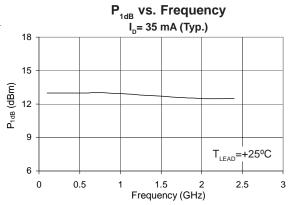
Parameter	Unit	100	500	850	1950	2400	3500
		MHz	MHz	MHz	MHz	MHz	MHz
Small Signal Gain	dB	28.2	27.1	25.0	19.7	18.3	14.8
Output Third Order Intercept Point	dBm	23.8	23.9	24.5	25.0	25.5	
Output Power at 1dB Compression	dBm	13.0	13.0	13.0	12.5	12.5	
Input Return Loss	dB	28.4	12.8	10.7	10.5	11.1	10.6
Output Return Loss	dB	31.5	17.1	15.9	20.5	20.3	18.9
Reverse Isolation	dB	29.4	29.0	28.1	24.1	22.4	19.2
Noise Figure	dB		2.4	2.5	2.5	2.5	

Test Conditions: I_D = 35 mA Typ., OIP $_3$ Tone Spacing = 1MHz, P_{OUT} per tone = -5dBm, R_{BIAS} = 100 Ω , T_L = 25 °C, Z_S = Z_L = 50 Ω

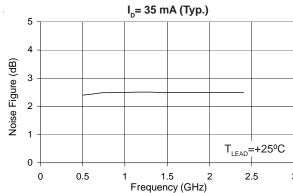






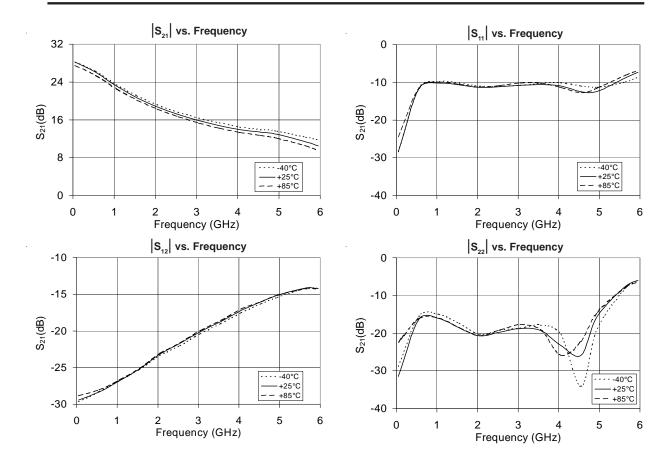


Noise Figure vs. Frequency





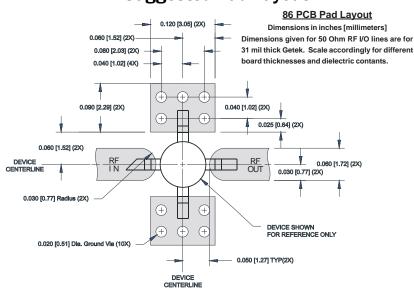
Typical RF Performance Over Lead Temperature -- Bias: I_D = 35 mA (Typ.) at T_{LEAD} = +25 $^{\circ}$ C





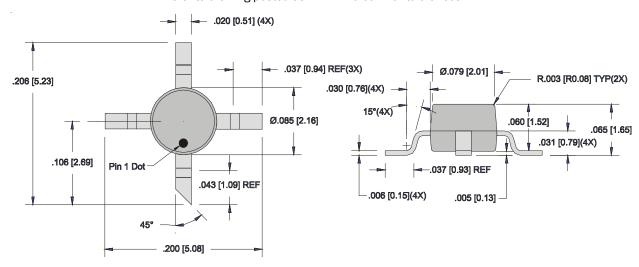
Pin	Function	Description	
1 RF IN RF input pin. This pin requires the use of an external DC-blocking capacitor chosen for the frequen			
2, 4	GND	Connection to ground. For optimum RF performance, use via holes as close to ground leads as possible to reduce lead inductance.	
		RF output and bias pin. DC voltage is present on this pin, therefor a DC-blocking capacitor is necessary for proper operation.	

Suggested Pad Layout



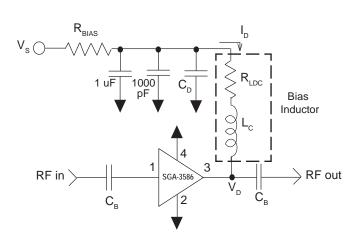
Package Drawing

Dimensions in inches (millimeters)
Refer to drawing posted at www.rfmd.com for tolerances.





Application Schematic



Application Circuit Element Values								
Reference	Frequency (Mhz)							
Designator	100	500	850	1950	2400	3500		
C _B	C _B 1000 pF		100 pF	68 pF	56 pF	39 pF		
C _D	100 pF	100 pF	68 pF	22 pF	22 pF	15 pF		
L _c	470 nH	68 nH	33 nH	22 nH	18 nH	15 nH		

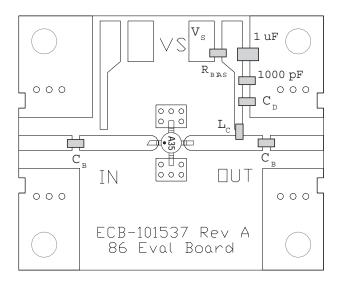
Recommended Bias Resistance for $I_D = 35 \text{ mA}$							
Supply Voltage (V _s) (Volts)	< 5	5	6	7	8	9	10
Bias Resistance* (Ohms)	N/R	50	79	107	136	164	193

* Bias Resistance = $R_{BIAS} + R_{LDC} = \overline{(V_S - V_D)/I_D}$

Select R_{BIAS} so that $R_{\text{BIAS}} + R_{\text{LDC}} \sim$ the recommended bias resistance. Use 1% or 5% tolerance resistsors or parallel combinations to attain the recommended bias resistance +/-3%. R_{BIAS} provides current stability over temperature.

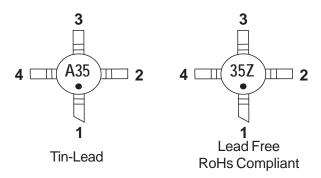
* N/R=Not Recommended. Contact Sirenza technical support for guidance when available supply voltage is less than 5 Volts.

Evaluation Board Layout





Part Identification



Ordering Information

Part Number	Package / Lead Composition	Reel Size	Devices / Reel	
SGA-3586	Tin-Lead	13"	3000	
SGA-3586Z	Lead Free, RoHs Compliant	13"	3000	

SGA-3586(Z)

